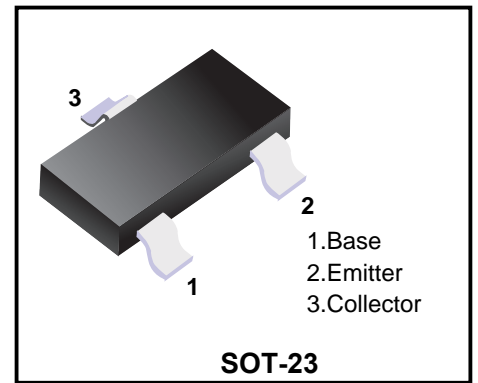
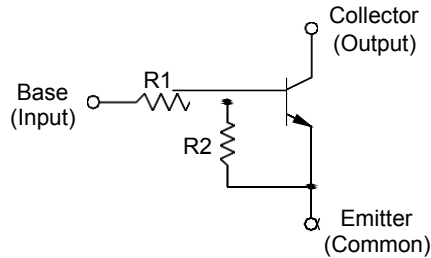


NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



Resistor Values

Type	Marking	R1 (KΩ)	R2 (KΩ)
KRC101S	NA	4.7	4.7
KRC102S	NB	10	10
KRC103S	NC	22	22
KRC104S	ND	47	47
KRC105S	NF	2.2	47
KRC106S	NE	4.7	47

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Output Voltage		V _O	50	V
Input Voltage	KRC101S	V _I	20, -10	V
	KRC102S		30, -10	
	KRC103S		40, -10	
	KRC104S		40, -10	
	KRC105S		12, -5	
	KRC106S		20, -5	
Output Current		I _O	100	mA
Total Power Dissipation		P _{tot}	200	mW
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	- 55 to + 150	°C

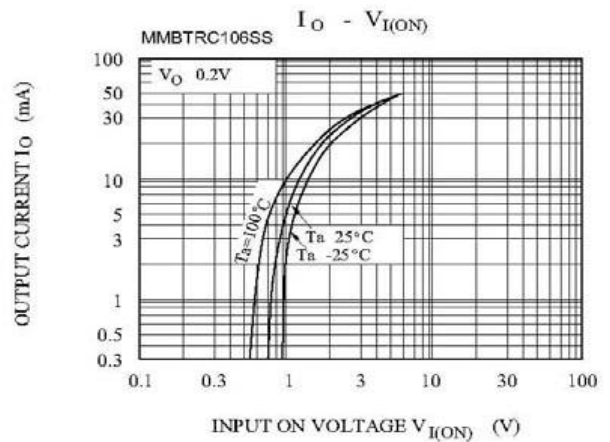
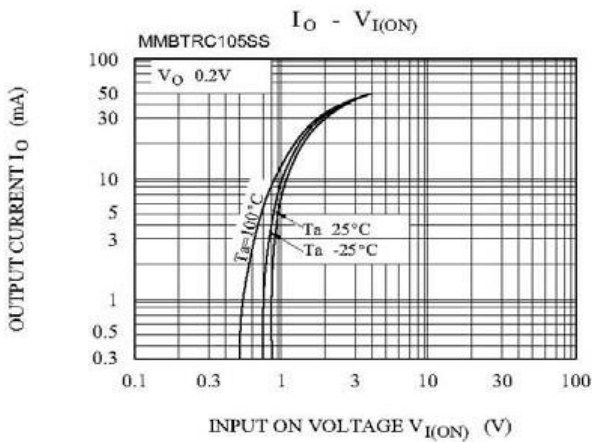
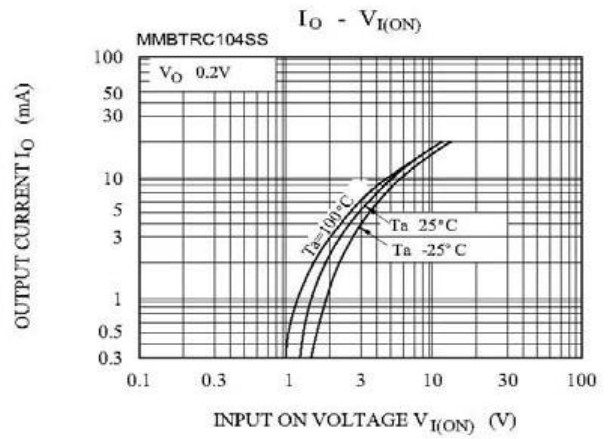
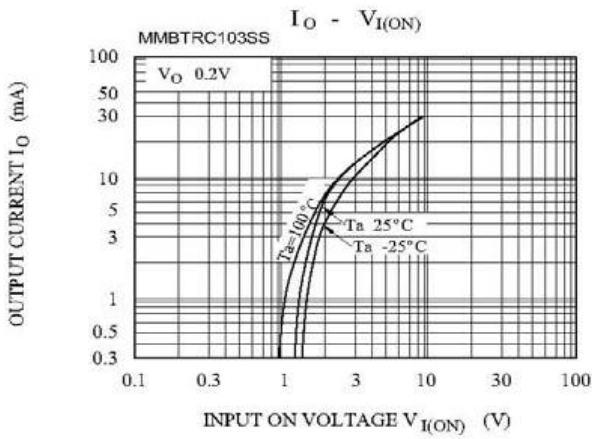
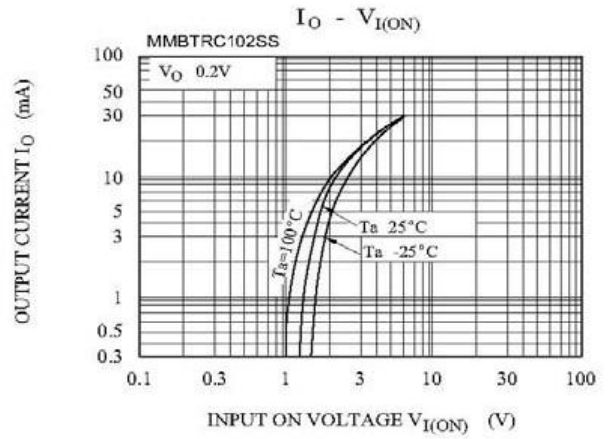
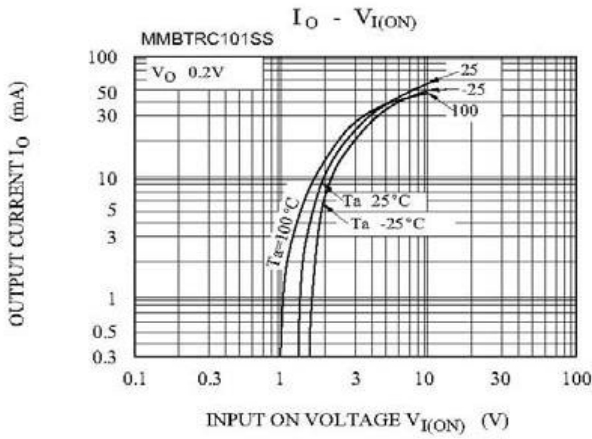
Marking

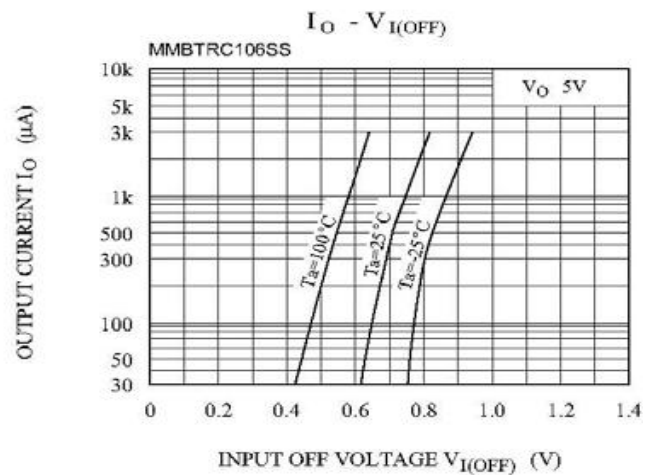
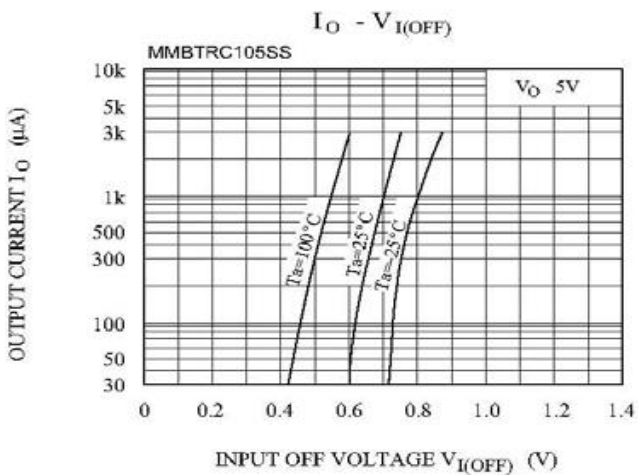
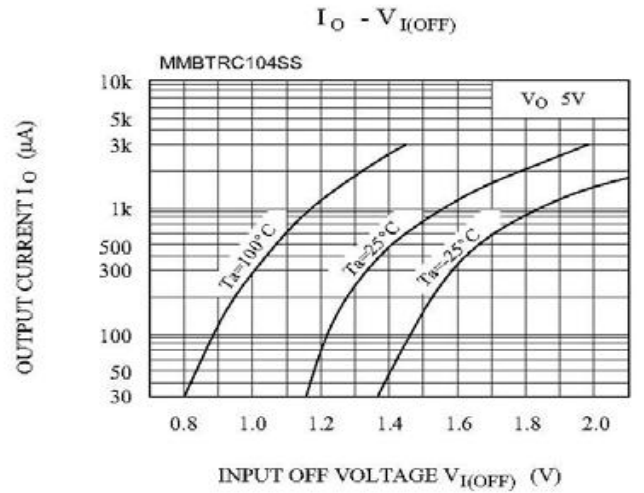
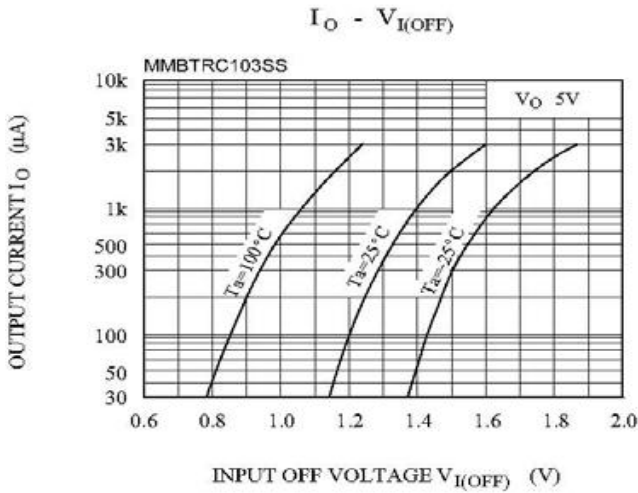
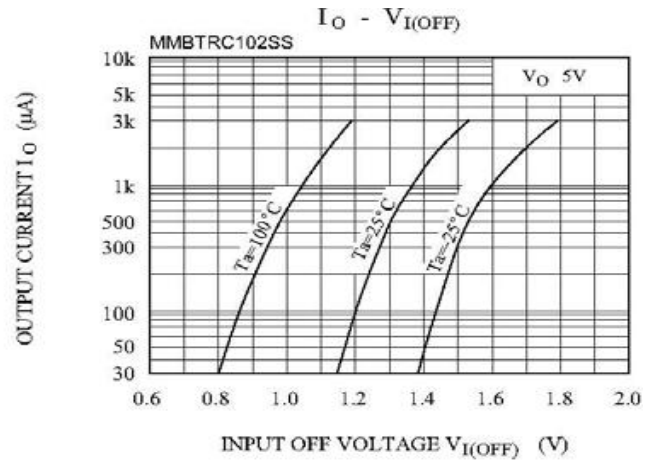
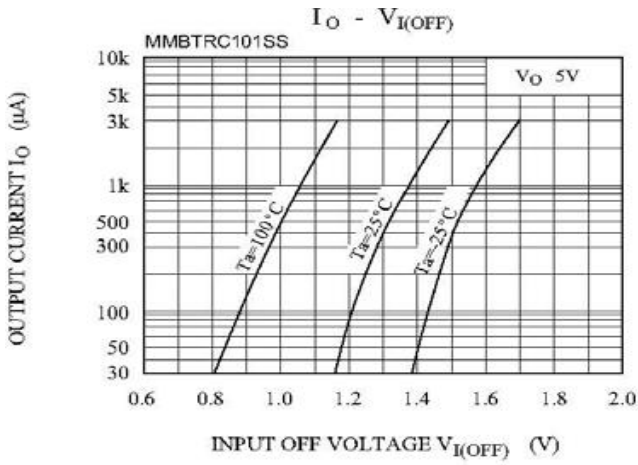
TYPE	KRC101S	KRC102S	KRC103S	KRC104S	KRC105S	KRC106S
MARK	NA	NB	NC	ND	NF	NE

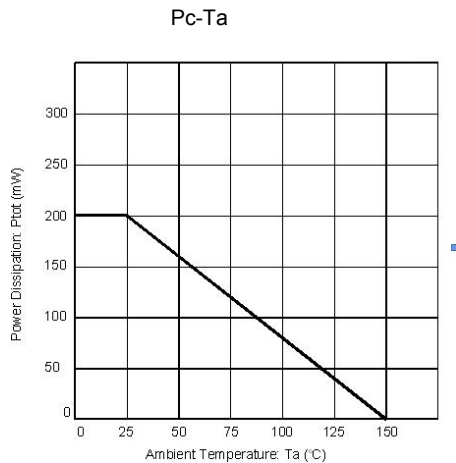
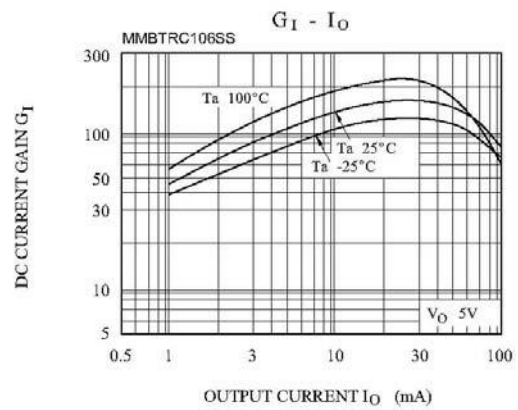
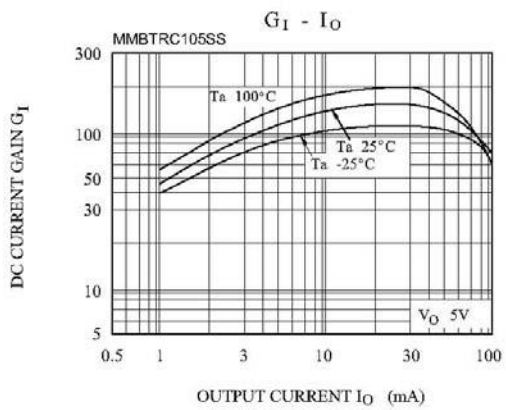
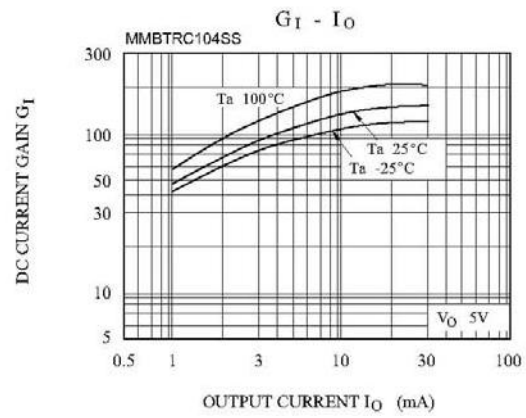
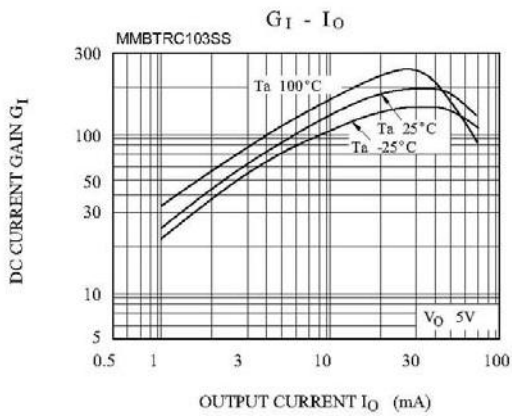
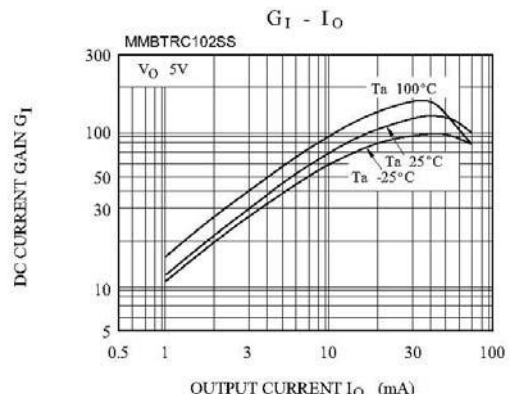
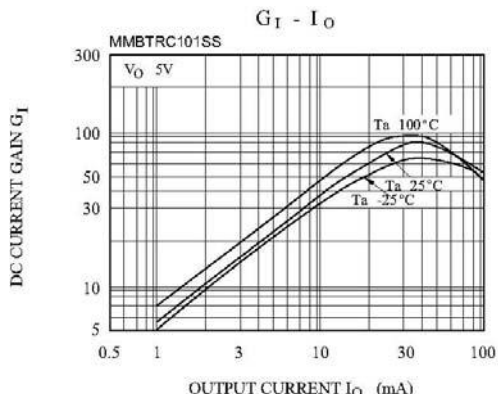
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_o = 5\text{ V}$, $I_o = 10\text{ mA}$	KRC101S KRC102S KRC103S KRC104S KRC105S KRC106S	30 50 70 80 80 80	- - - - - -	- - - - - -	- - - - - -
Output Cutoff Current at $V_o = 50\text{ V}$	$I_{O(OFF)}$	-	-	500	nA
Input Current at $V_i = 5\text{ V}$	KRC101S KRC102S KRC103S KRC104S KRC105S KRC106S	- - - - - -	- - - - - -	1.8 0.88 0.36 0.18 3.6 1.8	mA
Output Voltage at $I_o = 10\text{ mA}$, $I_i = 0.5\text{ mA}$	$V_{O(ON)}$	-	-	0.3	V
Input Voltage (ON) at $V_o = 0.2\text{ V}$, $I_o = 5\text{ mA}$	KRC101S KRC102S KRC103S KRC104S KRC105S KRC106S	- - - - - -	- - - - - -	2 2.4 3 5 1.1 1.3	V
Input Voltage (OFF) at $V_o = 5\text{ V}$, $I_o = 0.1\text{ mA}$	KRC101S~104S KRC105S~106S	1 0.5	- -	- -	V
Transition Frequency at $V_o = 10\text{ V}$, $I_o = 5\text{ mA}$	$f_T^{1)}$	-	200	-	MHz

1) Characteristic of transistor only.







Ordering information

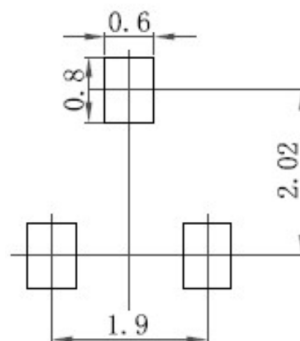
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



Disclaimer

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